## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re: Allen et al.

Serial No.: To Be Assigned Filed: Concurrently Herewith

For: METHODS OF FABRICATING SILICON CARBIDE METAL-

SEMICONDUCTOR FIELD EFFECT TRANSISTORS

Date: November 12, 2003

Mail Stop PATENT APPLICATION Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

## - PRELIMINARY AMENDMENT

Sir:

Please enter the following Preliminary Amendment before examining the present application.

Amendments to the Title begin on page 2 of this paper.

Amendments to the Specification begin on page 3 of this paper.

Amendments to the Claims are reflected in the listing of claims, which begins on page 4 of this paper.

Remarks begin on page 16 of this paper.

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Page 2 of 16

## In the Title:

Please delete the title in all occurrences and substitute the following title therefor: -- METHODS OF FABRICATING SILICON CARBIDE METAL-SEMICONDUCTOR FIELD EFFECT TRANSISTORS--.